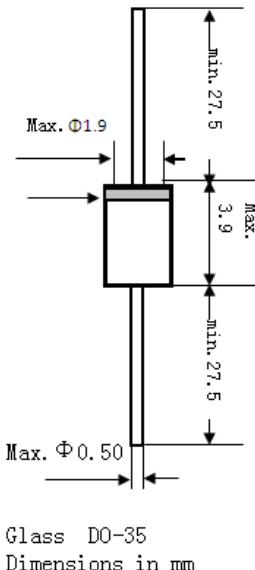


## YZPST-BAT85

## Schottky barrier single diode



## ABSOLUTE RATINGS(LIMITING VALUES)

	Symbols	Value	Units
Repetitive Peak Reverse Voltage	V <sub>R</sub>	30	V
Forward Continuous Current at T <sub>A</sub> =25°C	I <sub>F</sub>	200 <sup>1)</sup>	mA
Repetitive Peak Forward Current at t <sub>p</sub> <1s, δ<0.5, T <sub>A</sub> =25°C	I <sub>FM</sub>	300 <sup>1)</sup>	mA
Surge forward current at t <sub>p</sub> <10ms, T <sub>A</sub> =25°C	I <sub>FSM</sub>	600 <sup>1)</sup>	mA
Power Dissipation at T <sub>A</sub> =65°C	P <sub>tot</sub>	200 <sup>1)</sup>	mW
Junction temperature	T <sub>J</sub>	125	°C
Ambient Operating temperature Range	T <sub>A</sub>	-65 to+125	°C
Storage Temperature Range	T <sub>TSG</sub>	-65 to+150	°C

1) Valid provided that leads at a distance of 4mm from case are kept at ambient temperature

## ELECTRICAL CHARACTERISTICS

	Symbols	Min.	Typ.	Max.	Units
Reverse breakdown voltage Tested with 100µA pulses	V <sub>(BR)R</sub>	30			V
Forward voltage Pulse Test t <sub>p</sub> <300µs,δ<2% at I <sub>F</sub> =0.1mA, at I <sub>F</sub> =1mA, at I <sub>F</sub> =10mA, at I <sub>F</sub> =30mA, at I <sub>F</sub> =100mA	V <sub>F</sub>		0.50	0.24 0.32 0.4 0.8	V
Leakage current V <sub>R</sub> =25V	I <sub>R</sub>			2	µA
Junction Capacitance at V <sub>R</sub> =1V f=1MHz	C <sub>J</sub>			10	pF
Reverse recovery time Form I <sub>r</sub> =10mA, I <sub>f</sub> =10mA, I <sub>off</sub> =1mA	t <sub>rr</sub>			5	ns
Thermal resistance junction to ambient Air	R <sub>θJA</sub>			300 <sup>1)</sup>	K/W

1) Valid provided that leads at a distance of 4mm from case are kept at ambient temperature(DO-35)